Application No. 10/529.044

## IN THE CLAIMS:

Please AMEND claims 1, 3, 5, 7, 8, and 10, and please CANCEL claims 2, 6, 9, and 11 without prejudice or disclaimer in accordance with the following:

1. (CURRENTLY AMENDED) A high density recording medium with a superresolution near-field structure including a sequential stack of a second dielectric layer, a
recording layer, a protective layer, a mask layer, a first dielectric layer, and a polycarbonate layer,
wherein the mask layer comprises high-melting-point-metal-oxide-WO<sub>x</sub> to generate a near field
by optically or thermally inducing physical changes in the crystalline structure and optical
properties of the WO<sub>x</sub>high-melting-point-metal-oxide.

## 2. (CANCELED)

3. (CURRENTLY AMENDED)

A high density recording medium with a superresolution near-field structure including a sequential stack of a second dielectric layer, a
recording layer, a protective layer, a mask layer, a first dielectric layer, and a polycarbonate layer,
wherein the mask layer comprises TaO, or AuO, to generate a near field by optically or thermally
inducing physical changes in the crystalline structure and optical properties of the TaO, or
AuO, high-density recording medium of claim 1, wherein the high melting-point metal-oxide for
the mask layer is TaO, or AuO, which shows irreversible physical changes.

## 4. (CANCELED)

 (CURRENTLY AMENDED) The high density recording medium of claim 1, further comprising a reflective layer containing silver or aluminum below-disposed on an opposite side of the second dielectric layer from the recording layer.

## 6. (CANCELED)

7. (CURRENTLY AMENDED) The high density recording medium of claim 3,

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further comprising a reflective layer containing silver or aluminum below-disposed on an opposite side of the second dielectric layer from the recording layer.

- 8. (CURRENTLY AMENDED) A high density recording medium with a superresolution near-field structure including a sequential stack of a second dielectric layer, a recording layer, a protective layer, a mask layer, a first dielectric layer, and a polycarbonate layer, wherein the mask layer <u>consists of SiO</u>, eemprises-silicen-oxide-to generate a near field by optically or thermally inducing physical changes in the crystalline structure and optical properties of the silicon oxide.
  - 9. (CANCELED)
- 10. (CURRENTLY AMENDED) The high density recording medium of claim 8, further comprising a reflective layer containing silver or aluminum below-disposed on an opposite side of the second dielectric layer from the recording layer.
  - 11. (CANCELED)